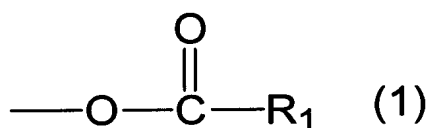


**Amendments to the Claims:**

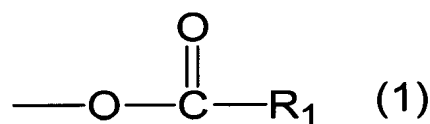
The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An underlayer coating forming composition comprising a crosslinking compound, an organic solvent and a dextrin ester compound,  
\_\_\_\_\_ wherein at least 50% of hydroxy groups in ~~the~~ dextrin are converted into ester groups of formula (1):



\_\_\_\_\_ wherein R<sub>1</sub> is C<sub>1-10</sub>alkyl group that may be substituted with a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C<sub>1-6</sub>alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, an iodine atom or a C<sub>1-6</sub>alkoxycarbonyl group, ~~group~~; or a phenyl group, a naphthyl group or an anthryl ~~group that group~~, each of which may be substituted with a C<sub>1-6</sub>alkyl group, a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C<sub>1-6</sub>alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, an iodine atom or a C<sub>1-6</sub>alkoxycarbonyl group, ~~a crosslinking compound, and an organic solvent, and~~  
\_\_\_\_\_ wherein the underlayer coating composition forms an underlayer coating of a photoresist in a lithography process.

2. (Currently Amended) An underlayer coating forming composition comprising a crosslinking compound, an organic solvent and a dextrin ester compound,  
\_\_\_\_\_ wherein at least 50% of hydroxy groups in ~~the~~ dextrin is converted into ester groups of formula (1):



\_\_\_\_\_ wherein R<sub>1</sub> is a C<sub>1-10</sub>alkyl group that may be substituted with a hydroxy group, a carboxyl group, a cyano group, a nitro group, a C<sub>1-6</sub>alkoxy group, a fluorine atom, a chlorine atom, a bromine atom, a iodine atom or a C<sub>1-6</sub>alkoxycarbonyl ~~group, group~~; or a phenyl group, a naphthyl group or an anthryl ~~group that group~~, each of which may be substituted with C<sub>1-6</sub>alkyl group, hydroxy group, carboxyl group, cyano group, nitro group, C<sub>1-6</sub>alkoxy group, fluorine atom, chlorine atom, bromine atom, iodine atom or C<sub>1-6</sub>alkoxycarbonyl group,

\_\_\_\_\_ wherein the dextrin ester compound has a weight average molecular weight of 4000 to 20000, and

\_\_\_\_\_ wherein the underlayer coating composition forms an underlayer coating of a photoresist in a lithography process, ~~and wherein the composition further comprises a crosslinking compound, and an organic solvent.~~

3. (Previously Presented) The underlayer coating forming composition according to claim 1, further comprising an acid compound or an acid generator.

4. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 1 on a semiconductor substrate, and baking it to form ~~an~~ the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

5. (Currently Amended) The underlayer coating forming composition according to claim 1, wherein the composition ~~is used for forming~~ forms an ~~the~~ underlayer coating by

coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

6. (Previously Presented) The underlayer coating forming composition according to claim 2, further comprising an acid compound or an acid generator.

7. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 2 on a semiconductor substrate, and baking it to form ~~an~~the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

8. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 3 on a semiconductor substrate, and baking it to form ~~an~~the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.

9. (Currently Amended) The underlayer coating forming composition according to claim 2, wherein the composition ~~is used for forming an~~forms the underlayer coating by coating the composition on a semiconductor substrate having a hole with an aspect ratio shown in height/diameter of 1 or more, and baking it.

10. (Currently Amended) A method for forming a photoresist pattern for use in manufacture of a semiconductor device, comprising:

coating the underlayer coating forming composition according to claim 6 on a semiconductor substrate, and baking it to form ~~an~~ the underlayer coating;

forming a photoresist layer on the underlayer coating;

exposing the semiconductor substrate covered with the underlayer coating and the photoresist layer to light; and

developing the photoresist layer after the exposure to light.